

Silicon Transistors

	Type No.	Case	Construction (see note 1)	Maximum Ratings at 25°C amb.			Characteristics							
				Interbase Voltage	I _E peak	P _{tot}	Intrinsic standoff ratio	Peak-current Emitter Current I _p at V _{B²B¹} = 25 V	Interbase Resistance T _{BBO}					
									Min.	Max.	Max. uA		Min.	Max.
				V	A	W				kohm				
Silicon Unijunction	2N489	TO5	G	65	2	0.6	0.51	0.62	20	4.7	6.8			
	2N489A	TO5	G	65	2	0.6	0.51	0.62	15	4.7	6.8			
	2N489B	TO5	G	65	2	0.6	0.51	0.62	6	4.7	6.8			
	2N490	TO5	G	65	2	0.6	0.51	0.62	20	6.2	9.1			
	2N490A	TO5	G	65	2	0.6	0.51	0.62	15	6.2	9.1			
	2N490B	TO5	G	65	2	0.6	0.51	0.62	6	6.2	9.1			
	2N491	TO5	G	65	2	0.6	0.56	0.68	20	4.7	6.8			
	2N491A	TO5	G	65	2	0.6	0.56	0.68	15	4.7	6.8			
	2N491B	TO5	G	65	2	0.6	0.56	0.68	6	4.7	6.8			
	2N492	TO5	G	65	2	0.6	0.56	0.68	20	6.2	9.1			
	2N492A	TO5	G	65	2	0.6	0.56	0.68	15	6.2	9.1			
	2N492B	TO5	G	65	2	0.6	0.56	0.68	6	6.2	9.1			
	2N493	TO5	G	65	2	0.6	0.62	0.75	20	4.7	6.8			
	2N493A	TO5	G	65	2	0.6	0.62	0.75	15	4.7	6.8			
	2N493B	TO5	G	65	2	0.6	0.62	0.75	6	4.7	6.8			
	2N494	TO5	G	65	2	0.6	0.62	0.75	20	6.2	9.1			
	2N494A	TO5	G	65	2	0.6	0.62	0.75	15	6.2	9.1			
	2N494B	TO5	G	65	2	0.6	0.62	0.75	6	6.2	9.1			
	2N1671	TO5	G	35	2	0.45	0.47	0.62	25	4.7	9.1			
	2N1671A	TO5	G	35	2	0.45	0.47	0.62	25	4.7	9.1			
	2N1671B	TO5	G	35	2	0.45	0.47	0.62	6	4.7	9.1			
	2N2160	TO5	G	35	2	0.45	0.47	0.80	25	4.0	12.0			
	2N3980	TO18	P	35	1	0.36	0.68	0.82	2	4.0	8.0			
	TIS43	SILECT	P	—	1	0.3	0.55	0.82	5	4.0	9.1			

	Type No.	Case	Construction (see note 1)	Maximum Ratings at 25°C amb.					Characteristics							SPECIAL FEATURES
				V _{CB} V	V _{CE} V	V _{EB} V	I _C A	P _{tot} W	V _{E1-E2}		r _{e1-e2(ON)}		f _t		C _{OB} pf Max.	
									I _{fl} mA	Max. V	I _{fl} mA	Max. Ω	I _{fl} mA	Min. Mc		
PNP High Speed Choppers	3N108	TO72	PE	−50	−50	−50	0.02	0.3	−1.0	30	−1.0	50	−1.0	12	10	DUAL EMITTERS
	3N109	TO72	PE	−50	−50	−50	0.02	0.3	−1.0	150	−1.0	50	−1.0	12	10	
	3N110	TO72	PE	−50	−30	−30	0.02	0.3	−1.0	30	−1.0	50	−1.0	12	10	
	3N111	TO72	PE	−50	−30	−30	0.02	0.3	−1.0	150	−1.0	50	−1.0	12	10	
NPN High Speed Choppers	3N74	TO72	P	50	18	18	0.02	0.30	1.0	50	1.0	40	1.0	30	8	DUAL EMITTERS
	3N75	TO72	P	50	18	18	0.02	0.30	1.0	100	1.0	40	1.0	30	8	
	3N76	TO72	P	50	18	18	0.02	0.30	1.0	200	1.0	50	1.0	30	8	
	3N77	TO72	P	40	12	12	0.02	0.30	1.0	50	1.0	50	1.0	30	8	
	3N78	TO72	P	40	12	12	0.02	0.30	1.0	100	1.0	50	1.0	30	8	
	3N79	TO72	P	40	12	12	0.02	0.30	1.0	200	1.0	60	1.0	30	10	

NOTE 1: The following symbols have been used throughout the Product Summary:

Under "Construction":	Under h _{FE} :	Under f _T :	Under Dissipation:
A — Alloyed	* — h _{FE}	φ — f _{hfb}	† — dissipation at T _{case} = 25°C
D — Diffused		Δ — f _{hfe}	
E — Epitaxial		‡ — typical	
G — Grown			
M — Mesa			
P — Planar			